

2MBI300XNA170-50

IGBT Modules

Power Module (X series)
1700V / 300A / 2-in-1 package



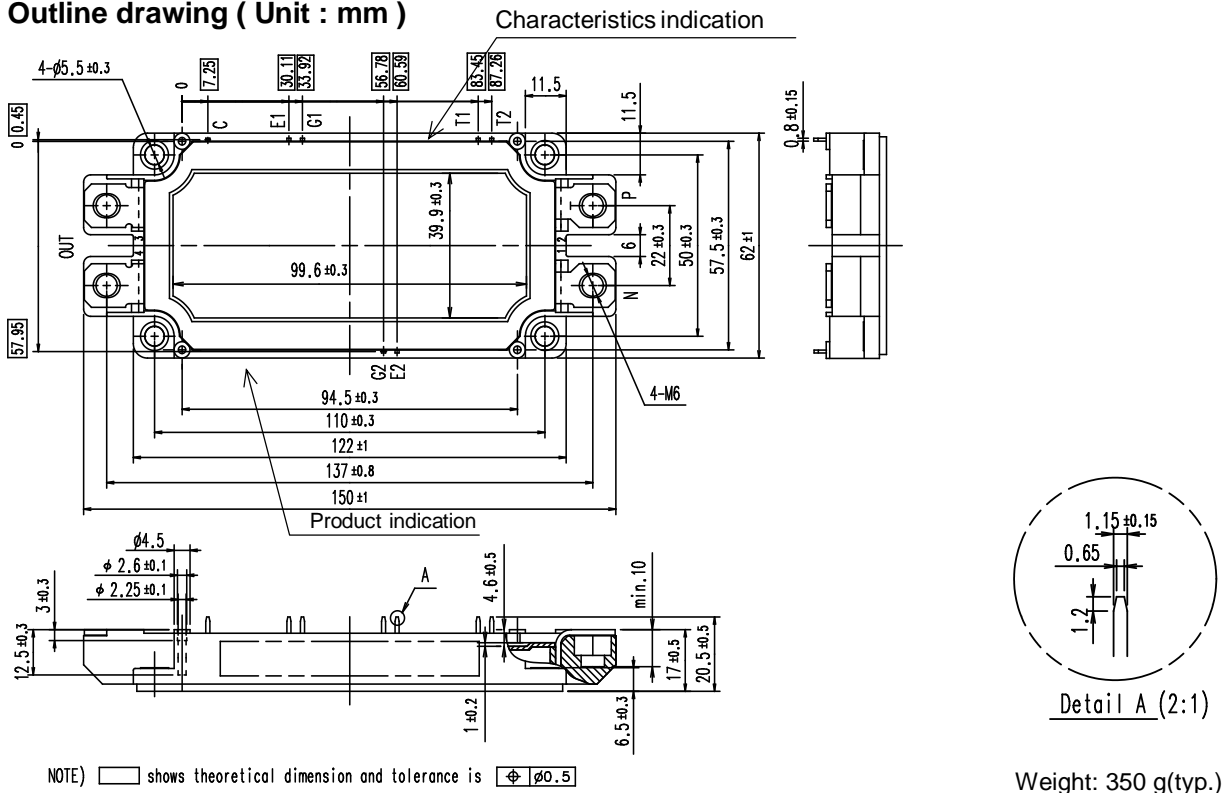
■ **Features**

- Low $V_{CE(sat)}$
- Low Inductance Module structure
- Solder pin terminals

■ **Applications**

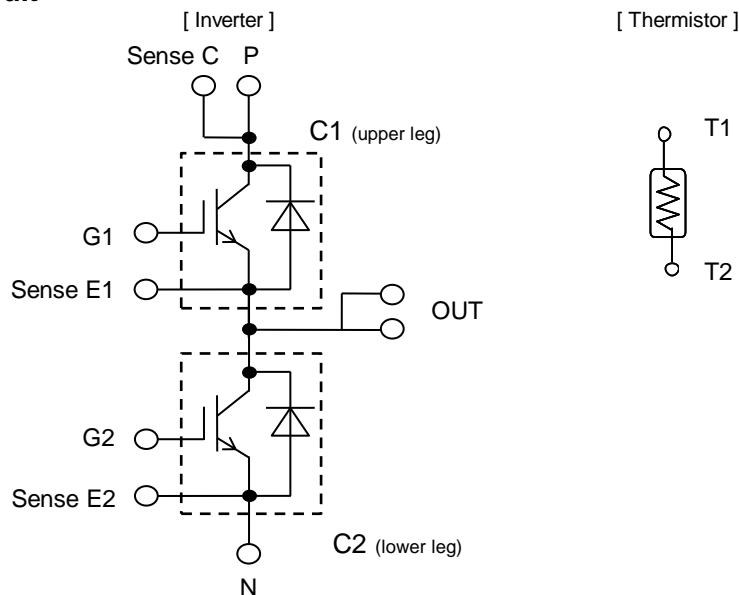
- Inverter for Motor Drives, AC and DC Servo Drives
- Uninterruptible Power Supply Systems, Wind Turbines, PV Power Conditioning Systems

■ **Outline drawing (Unit : mm)**



Weight: 350 g(typ.)

■ **Equivalent circuit**



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■ Absolute maximum ratings (at $T_C=25^\circ\text{C}$ unless otherwise specified)

Items		Symbols	Conditions	Maximum ratings	Units
Collector-Emitter voltage, Gate-Emitter short-circuited		V_{CES}		1700	V
Gate-Emitter voltage, Collector-Emitter short-circuited		V_{GES}		± 20	V
Collector current		I_C	Continuous $T_C=100^\circ\text{C}$	300	A
Repetitive peak collector current		I_{CRM}	1ms	600	
Forward current		I_F		300	
Repetitive peak forward current		I_{FRM}	1ms	600	
Total power dissipation		P_{tot}	1 device	1720	
Virtual junction temperature		T_{vj}		175	°C
Operating junction temperature (under switching conditions)		T_{vjop}		175	
Case temperature		T_c		125	
Storage temperature		T_{stg}		-40 ~ 125	
Isolation voltage	between terminal and copper base (*1)	V_{isol}	AC: 1min.	3400	Vrms
	between thermistor and others (*2)				
Mounting torque of screws to heatsink (*3)		M_s	M5	6.0	N·m
Mounting torque of screws to terminals (*3)		M_t	M6	6.0	

(*1) All terminals should be connected together during the test.

(*2) Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

(*3) Recommendable Value: : Mounting torque of screws to heatsink 2.5 ~ 6.0 N·m (M5)
Recommendable Value: : Mounting torque of screws to terminals 3.5 ~ 6.0 N·m (M6)

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■ Electrical characteristics (at $T_{vj}=25^{\circ}\text{C}$ unless otherwise specified)

Items	Symbols	Conditions	Characteristics			Units	
			min.	typ.	max.		
Collector-Emitter cut-off current, Gate-Emitter short-circuited	I_{CES}	$V_{GE} = 0\text{V}$ $V_{CE} = 1700\text{V}$	-	-	150	μA	
Gate leakage current, Collector-Emitter short-circuited	I_{GES}	$V_{CE}=0\text{V}, V_{GE}=\pm 20\text{V}$	-	-	300	nA	
Gate-Emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = 20\text{V}$ $I_C = 300\text{mA}$	6.0	6.5	7.0	V	
Collector-Emitter saturation voltage	$V_{CE(sat)}$ (terminal)	$V_{GE} = 15\text{V}$ $I_C = 300\text{A}$	$T_{vj}=25^{\circ}\text{C}$	-	1.95	2.40	V
	$V_{CE(sat)}$ (chip)		$T_{vj}=25^{\circ}\text{C}$	-	1.60	2.05	
			$T_{vj}=125^{\circ}\text{C}$	-	2.00	-	
			$T_{vj}=150^{\circ}\text{C}$	-	2.10	-	
			$T_{vj}=175^{\circ}\text{C}$	-	2.20	-	
Internal gate resistance	r_g	-	-	3.33	-	Ω	
Capacitance	C_{ies}	$V_{CE}=10\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}$	-	41	-	nF	
	C_{oes}		-	1.1	-		
	C_{res}		-	0.25	-		
Gate charge	Q_G	$V_{CC} = 900\text{V}, I_C = 300\text{A}$ $V_{GE} = -15 \rightarrow +15\text{V}$	-	2.1	-	μC	
Forward voltage	V_F (terminal)	$V_{GE} = 0\text{V}$ $I_F = 300\text{A}$	$T_{vj}=25^{\circ}\text{C}$	-	2.05	2.50	V
	V_F (chip)		$T_{vj}=25^{\circ}\text{C}$	-	1.70	2.15	
			$T_{vj}=125^{\circ}\text{C}$	-	1.80	-	
			$T_{vj}=150^{\circ}\text{C}$	-	1.85	-	
			$T_{vj}=175^{\circ}\text{C}$	-	1.80	-	
Switching time (*1)	$t_{d(on)}$	$V_{CC} = 900\text{V}$ $I_C, I_F = 300\text{A}$ $V_{GE} = \pm 15\text{V}$ $R_G = \pm 0.68\Omega$ $L_S = 35\text{ nH}$	$T_{vj}=25^{\circ}\text{C}$	-	0.39	-	μs
			$T_{vj}=125^{\circ}\text{C}$	-	0.43	-	
			$T_{vj}=150^{\circ}\text{C}$	-	0.43	-	
			$T_{vj}=175^{\circ}\text{C}$	-	0.44	-	
	t_r		$T_{vj}=25^{\circ}\text{C}$	-	0.07	-	
			$T_{vj}=125^{\circ}\text{C}$	-	0.09	-	
			$T_{vj}=150^{\circ}\text{C}$	-	0.09	-	
			$T_{vj}=175^{\circ}\text{C}$	-	0.09	-	
	$t_{d(off)}$		$T_{vj}=25^{\circ}\text{C}$	-	0.47	-	
			$T_{vj}=125^{\circ}\text{C}$	-	0.54	-	
			$T_{vj}=150^{\circ}\text{C}$	-	0.56	-	
			$T_{vj}=175^{\circ}\text{C}$	-	0.57	-	
	t_f		$T_{vj}=25^{\circ}\text{C}$	-	0.42	-	
$T_{vj}=125^{\circ}\text{C}$		-	0.61	-			
$T_{vj}=150^{\circ}\text{C}$		-	0.65	-			
$T_{vj}=175^{\circ}\text{C}$		-	0.70	-			
Reverse recovery time	t_{rr}	$T_{vj}=25^{\circ}\text{C}$	-	0.24	-		
		$T_{vj}=125^{\circ}\text{C}$	-	0.46	-		
		$T_{vj}=150^{\circ}\text{C}$	-	0.46	-		
		$T_{vj}=175^{\circ}\text{C}$	-	0.53	-		

(*1) Turn on time (t_{on}) = $t_{d(on)}+t_r$, Turn off time (t_{off}) = $t_{d(off)}+t_f$

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■ Electrical characteristics (at $T_{vj}= 25^{\circ}\text{C}$ unless otherwise specified)

Items	Symbols	Conditions	Characteristics			Units	
			min.	typ.	max.		
Switching loss (per pulse)	E_{on}	$V_{CC} = 900\text{V}$ $I_C, I_F = 300\text{A}$ $V_{GE} = \pm 15\text{V}$ $R_G = \pm 0.68\Omega$ $L_S = 35\text{nH}$	$T_{vj}=25^{\circ}\text{C}$	-	70	-	mJ
			$T_{vj}=125^{\circ}\text{C}$	-	95	-	
			$T_{vj}=150^{\circ}\text{C}$	-	103	-	
			$T_{vj}=175^{\circ}\text{C}$	-	117	-	
	E_{off}		$T_{vj}=25^{\circ}\text{C}$	-	61	-	
			$T_{vj}=125^{\circ}\text{C}$	-	86	-	
			$T_{vj}=150^{\circ}\text{C}$	-	92	-	
			$T_{vj}=175^{\circ}\text{C}$	-	103	-	
	E_{rr}		$T_{vj}=25^{\circ}\text{C}$	-	43	-	
			$T_{vj}=125^{\circ}\text{C}$	-	72	-	
			$T_{vj}=150^{\circ}\text{C}$	-	89	-	
			$T_{vj}=175^{\circ}\text{C}$	-	101	-	
Thermistor Resistance	R	$T = 25^{\circ}\text{C}$	-	5000	-	Ω	
		$T = 100^{\circ}\text{C}$	465	495	520		
Thermistor B value	B	$T = 25/ 50^{\circ}\text{C}$	3305	3375	3450	K	

NOTICE:

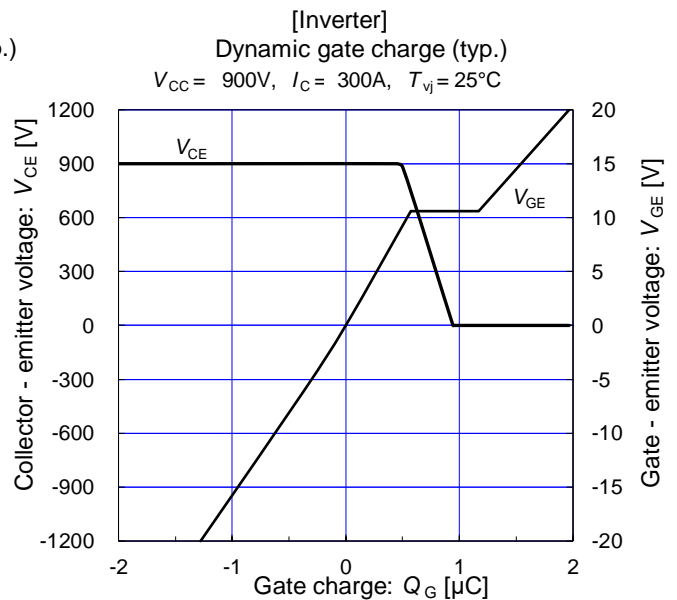
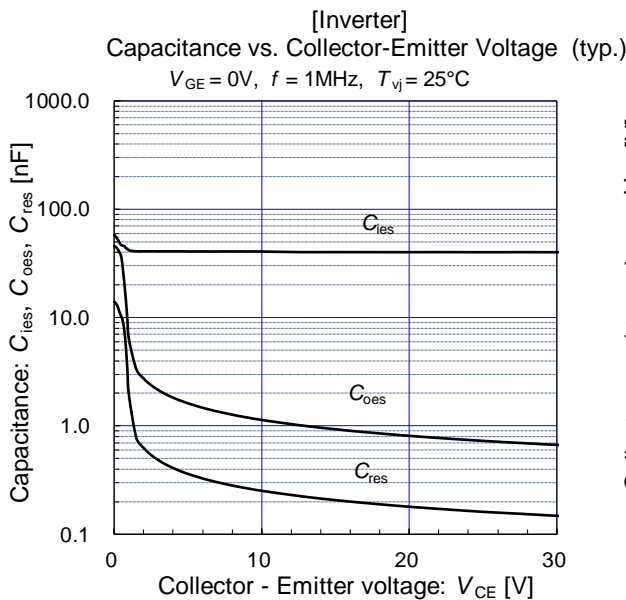
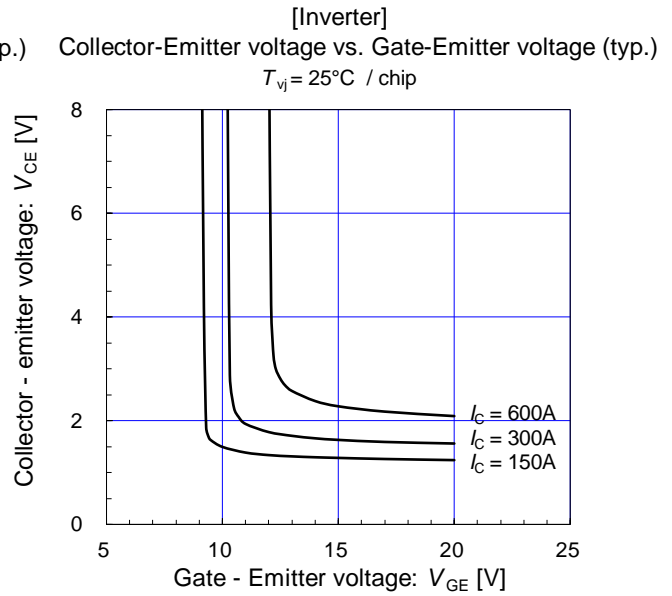
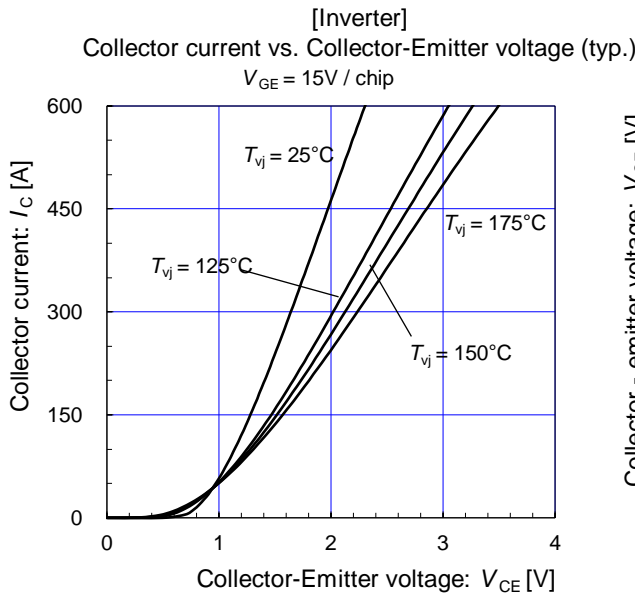
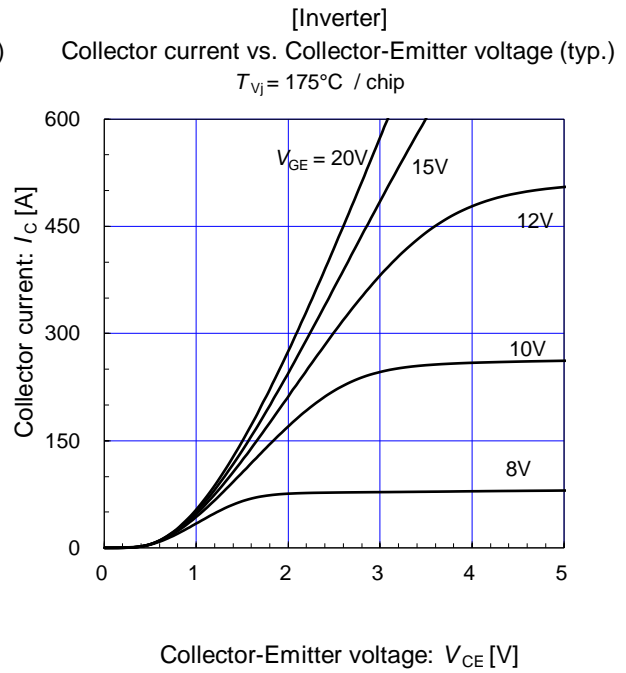
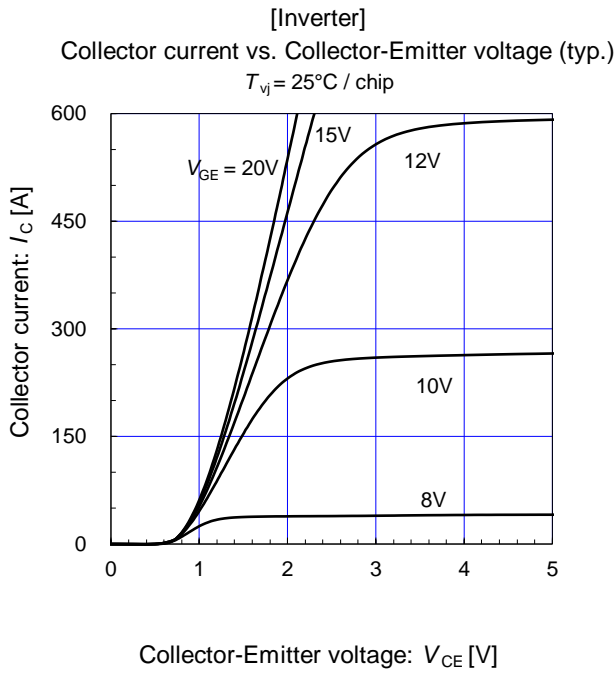
The external gate resistance (R_G) shown above is one of our recommended value for the purpose of minimum switching loss. However the optimum R_G depends on circuit configuration and/or environment. We recommend that the R_G has to be carefully chosen based on consideration if IGBT module matches design criteria, for example, switching loss, EMC/EMI, spike voltage, surge current and no unexpected oscillation and so on.

■ Thermal resistance characteristics

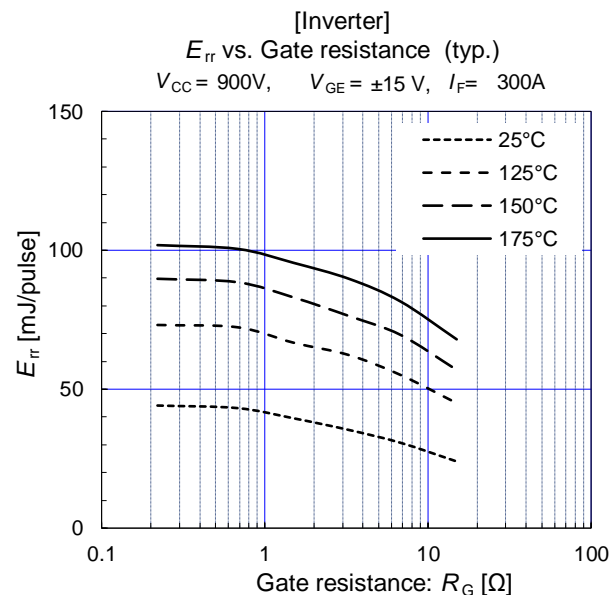
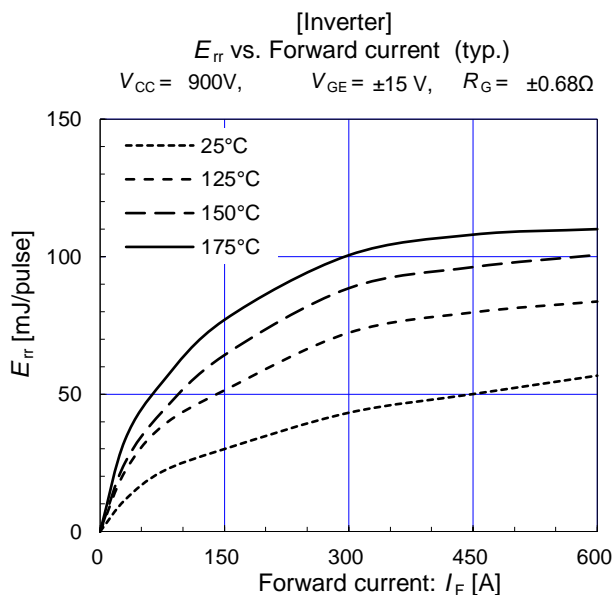
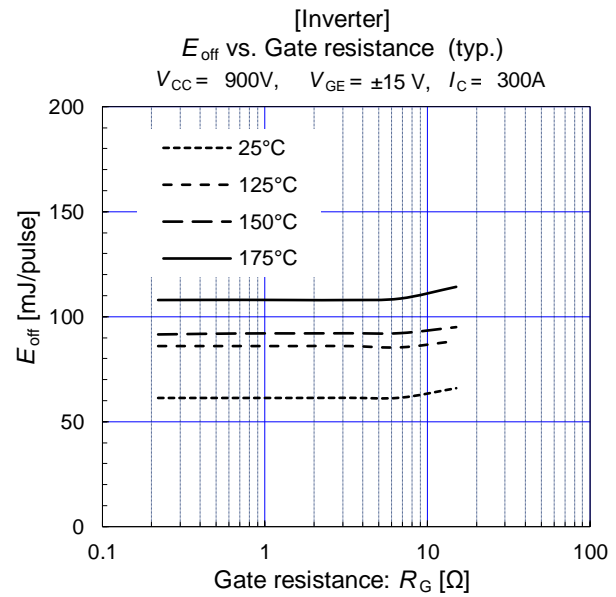
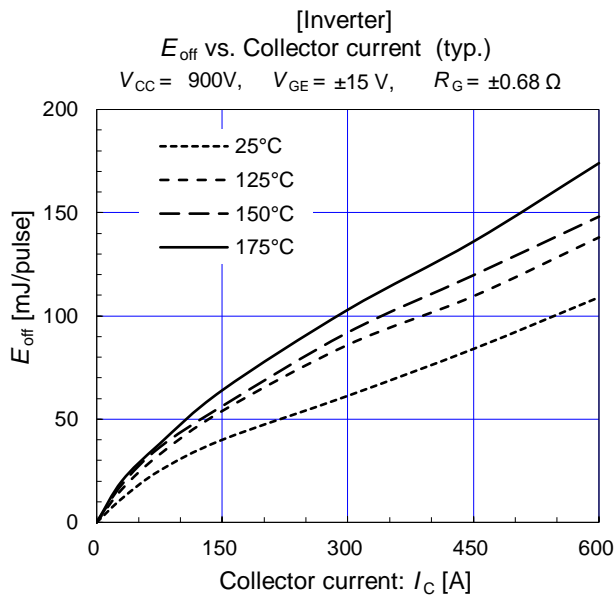
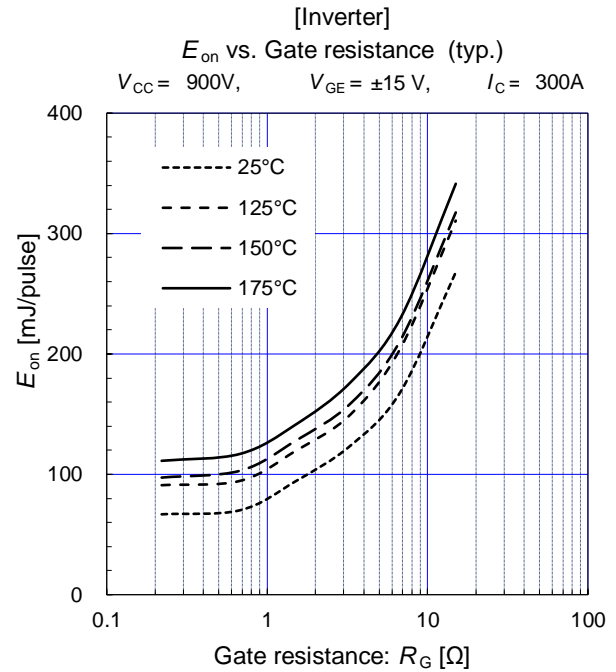
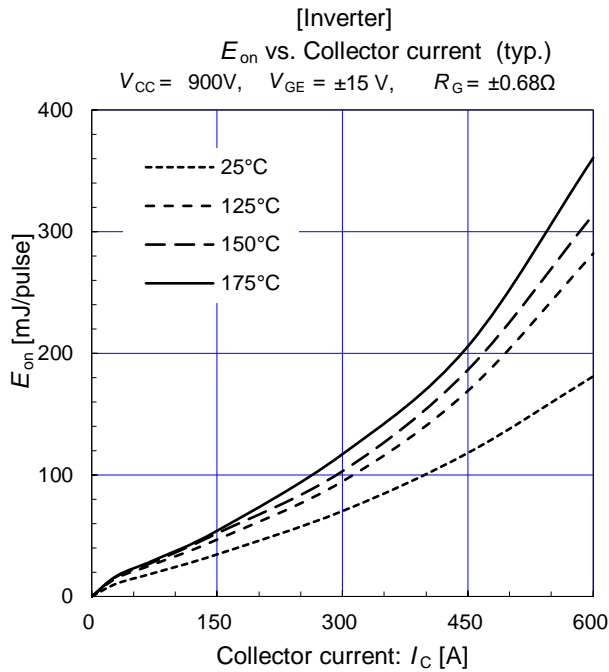
Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance junction to case(1 device)	$R_{th(j-c)}$	Inverter IGBT	-	-	0.087	K/W
		Inverter FWD	-	-	0.126	
Thermal resistance case to heatsink(1 IGBT+1 FWD) (*1)	$R_{th(c-s)}$	with 1 W/(m·K) thermal grease	-	0.0167	-	

(*1) This is the value which is defined mounting on the additional heatsink with thermal grease.

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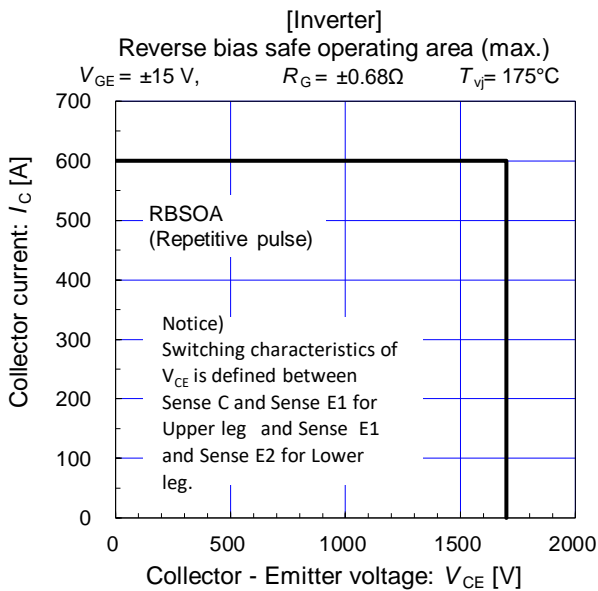
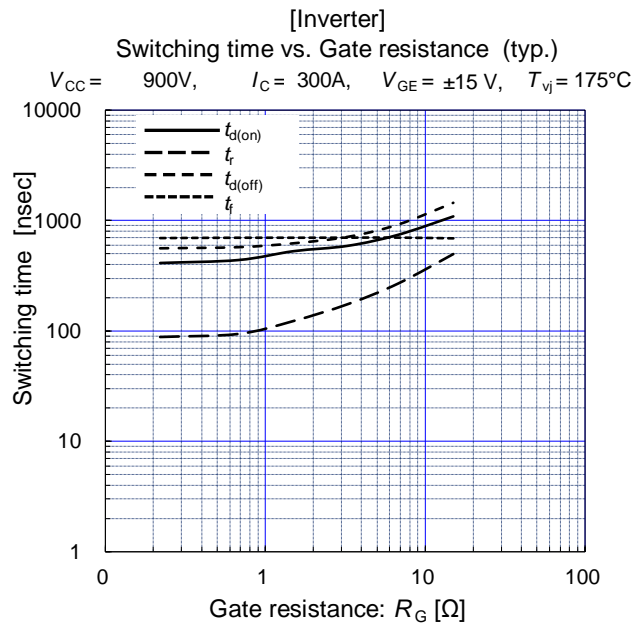
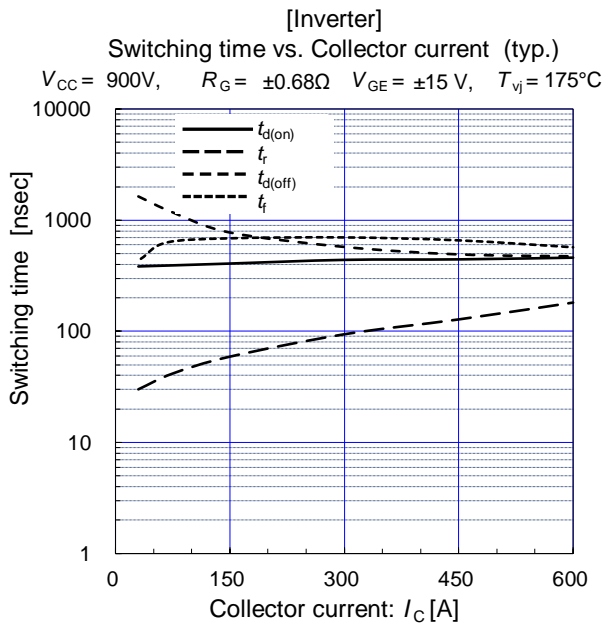
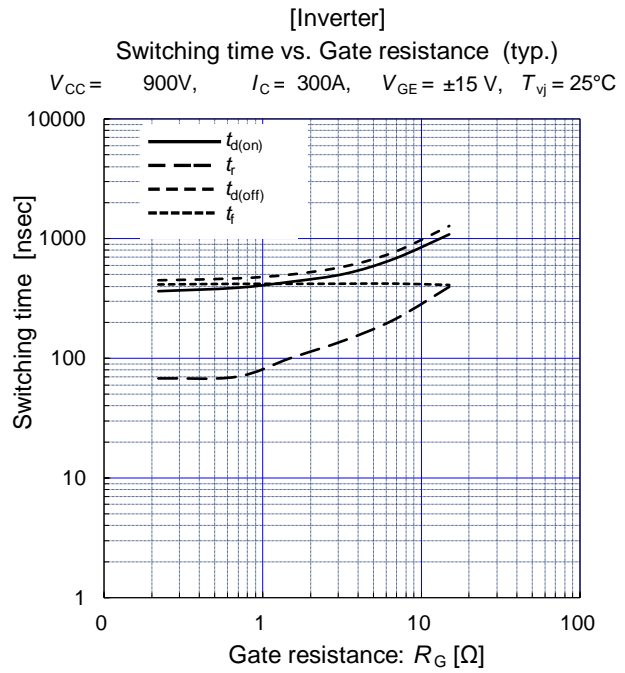
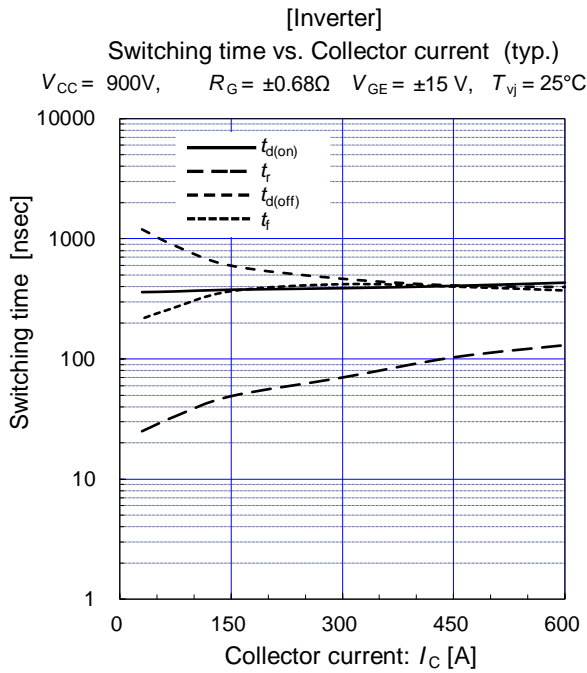


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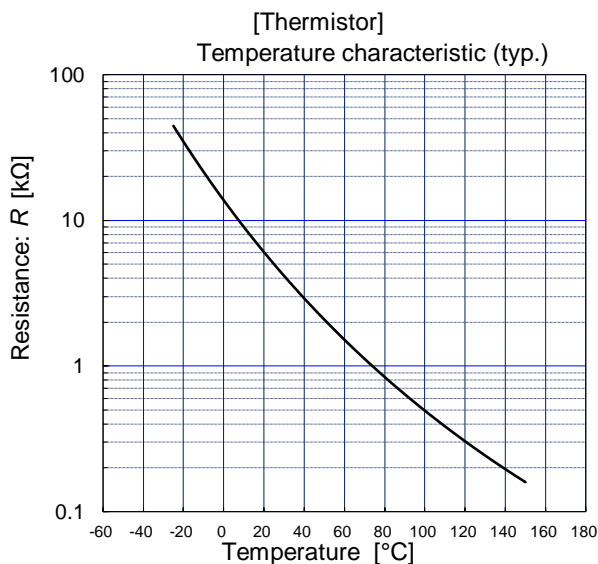
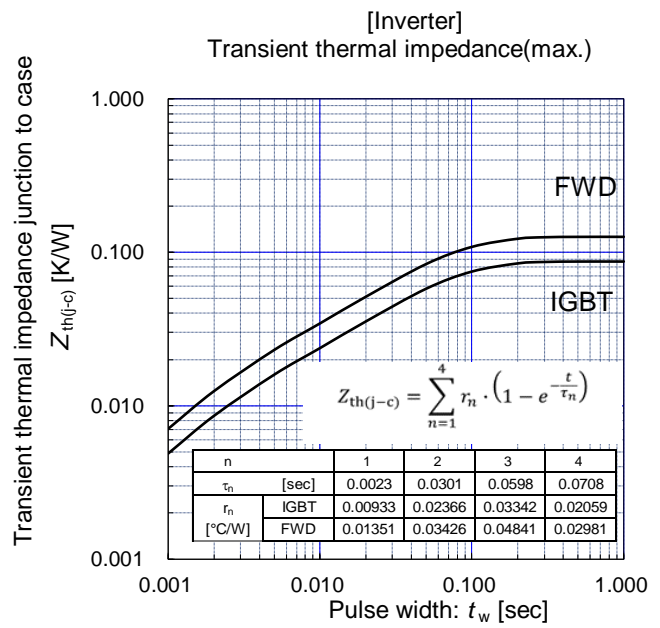
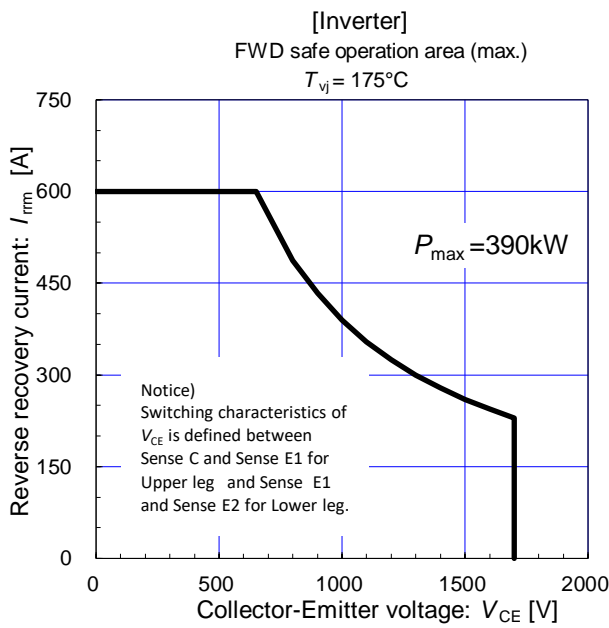
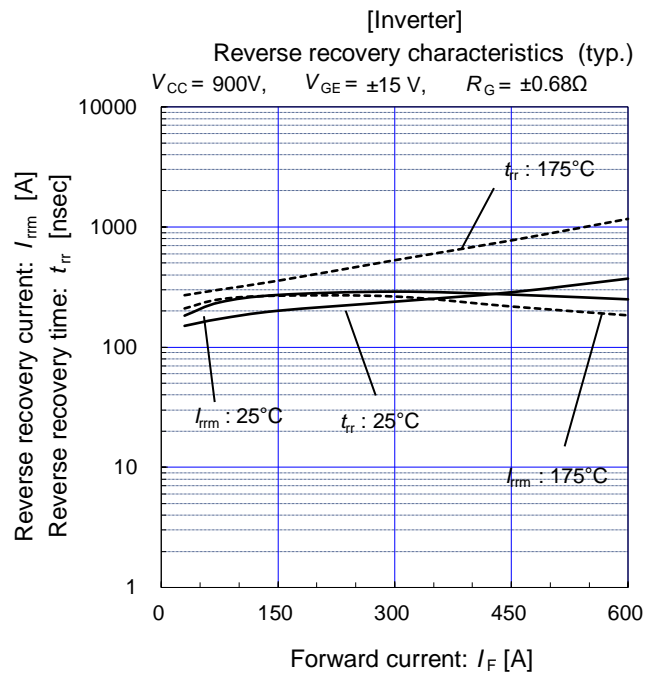
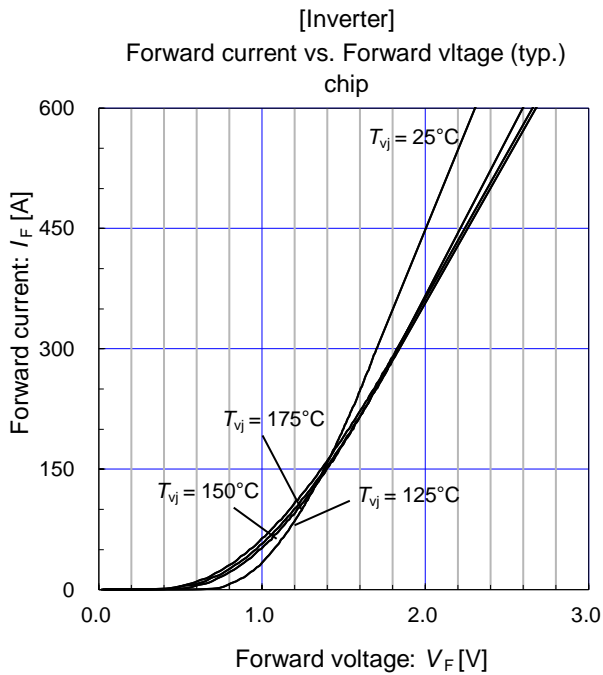
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